

Technical Data Green Products

Data Sheet N1218, Rev. B

309CMQ135/309CMQ150 SCHOTTKY RECTIFIER

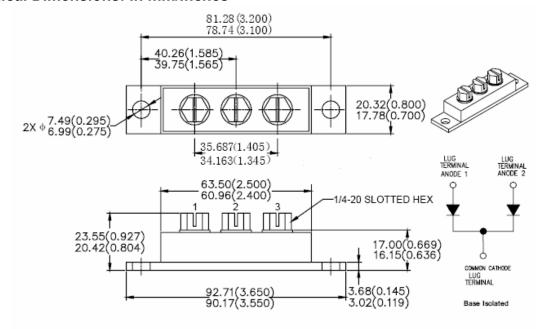
Applications:

- High current switching power supply Plating power supply Free-Wheeling diodes
- Reverse battery protection Converters UPS System Welding

Features:

- 175 °C T_J operation
- Center tap module
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- · Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm/Inches



Please Note: Anode 1 = Terminal 1; Anode 2 = Terminal 3; Common Cathode = Terminal 2 Suffix R Denotes for Reversed Polarity.

PRM4 (Isolated)

MARKING, MOLDING RESIN

Marking for 309CMQ135/150, 1st row SS YYWWL, 2nd row 309CMQ135/150 Where YY is the manufacture year

WW is the manufacture week code

L is the wafer's Lot Number

Molding resin

Epoxy resin UL:94V-0

[•] Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 🗏 (86) 25-87123907 •

[•] FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •



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Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Inverse Voltage	V_{RWM}	-	135	309CMQ135	V
			150	309CMQ150	
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =110°C,	150	per leg	Α
Current		rectangular wave form	300	per device	
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	1440		А

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	 @ 150A, Pulse, T_J = 25 °C @ 300A, Pulse, T_J = 25 °C 	1.03 1.22	V
	V_{F2}	 @ 150A, Pulse, T_J = 125 °C @ 300A, Pulse, T_J = 125 °C 	0.71 0.82	V
Max. Reverse Current (per	I _{R1}	$@V_R = \text{rated } V_R T_J = 25 ^{\circ}\text{C}$	3	mA
leg) *	I_{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	45	mΑ
Max. Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	4000	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	7.0	nΗ
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

^{*} Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

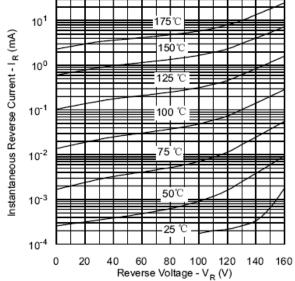
Characteristics	Symbol	Condition	Specifi	Units			
Max. Junction Temperature	T_J	-	-55 to	°C			
Max. Storage Temperature	T _{stg}	-	-55 to	°C			
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ heta JC}$	DC operation	0.5	°C/W			
Maximum Thermal Resistance Junction to Case (per package)	$R_{ heta JC}$	DC operation	0.25		°C/W		
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.10		°C/W		
Mounting Torque	Тм	-	Mounting Torque Terminal Torque	24(min) 35(max) 35(min) 46(max)	Kg-cm		
Approximate Weight	wt	-	79		g		
Case Style	PRM4 Isolated						

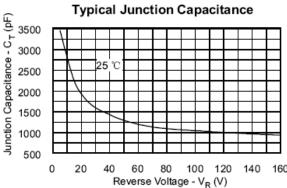


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Typical Forward Characteristics 10¹ Instantaneous Reverse Current - IR (mA) 10² 10⁰ 175 ℃ 10⁻¹ Instantaneous Forward Current - I_F (A) 10¹ 10⁻² 10⁻³ 10⁰ 10-4 0 Junction Capacitance - C_T (pF) 3500 10⁻¹ 3000 2500 2000 1500 10⁻² 1000 500 0.0 0.4 1.0 0.2 0.6 0.8 0 Forward Voltage Drop - V_F (V)

Typical Reverse Characteristics





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